

**BISMOS SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF**ABSTRACT OF THE DISCLOSURE

In a BiMOS semiconductor device, emitter and base electrodes formed by polycrystalline Si of a bipolar transistor are isolated from each other by way of a sidewall and an insulator layer. As this insulator layer acts as an offset during the formation of the sidewall, its layer thickness can be made larger. Further, as this insulator layer is not provided in a MOS region, its step can be made smaller. Consequently, parasitic capacitance can be reduced while the insulator layer can be made thicker. Thus, there can be achieved both fast operation and high reliability of the bipolar transistor and, moreover, reduction in the reliability of a MOS transistor can also be prevented.

